


BCR3AS

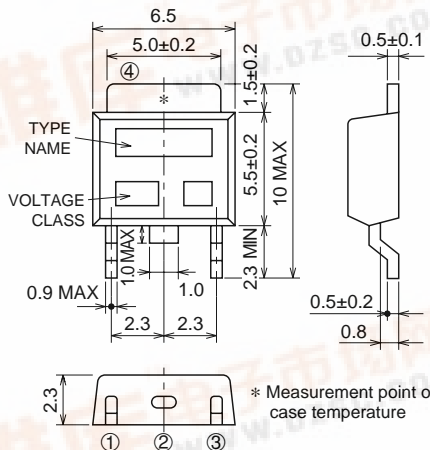
LOW POWER USE
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

BCR3AS



- I_T (RMS) **3A**
- V_{DRM} **400V/600V**
- $I_{FGT I}, I_{RGT I}, I_{RGT III}$ **15mA (10mA) *2**

OUTLINE DRAWING Dimensions in mm



* Measurement point of case temperature

① T1 TERMINAL
② T2 TERMINAL
③ GATE TERMINAL
④ T2 TERMINAL

MP-3

APPLICATION

Hybrid IC, solid state relay, switching mode power supply, light dimmer, electric fan, electric blankets, control of household equipment such as washing machine, other general purpose control applications

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8	12	
V_{DRM}	Repetitive peak off-state voltage *1	400	600	V
V_{DSM}	Non-repetitive peak off-state voltage *1	500	720	V

Symbol	Parameter	Conditions	Ratings	Unit
I_T (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction, $T_c=108^\circ\text{C}$	3	A
I_{TSM}	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	30	A
I_t^2	I_t^2 for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	3.7	A^2s
PGM	Peak gate power dissipation		3	W
PG (AV)	Average gate power dissipation		0.3	W
VGM	Peak gate voltage		6	V
IGM	Peak gate current		0.3	A
T_j	Junction temperature		-40 ~ +125	$^\circ\text{C}$
T_{stg}	Storage temperature		-40 ~ +125	$^\circ\text{C}$
—	Weight	Typical value	0.26	g

*1 Gate open.



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ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
IDRM	Repetitive peak off-state current	T _j =125°C, V _{DRM} applied	—	—	2.0	mA	
V _{TM}	On-state voltage	T _c =25°C, I _{TM} =4.5A, Instantaneous measurement	—	—	1.7	V	
V _{FGT I}	Gate trigger voltage *2	T _j =25°C, V _D =6V, R _L =6Ω, R _G =330Ω	I	—	—	1.5	V
V _{RGT I}			II	—	—	1.5	V
V _{RGT III}			III	—	—	1.5	V
I _{FGT I}	Gate trigger current *2	T _j =25°C, V _D =6V, R _L =6Ω, R _G =330Ω	I	—	—	15*2	mA
I _{RGT I}			II	—	—	15*2	mA
I _{RGT III}			III	—	—	15*2	mA
V _{GD}	Gate non-trigger voltage	T _j =125°C, V _D =1/2V _{DRM}	0.2	—	—	V	
R _{th(j-c)}	Thermal resistance	Junction to case *4	—	—	3.8	°C/W	
(dv/dt) _c	Critical-rate of rise of off-state commutating voltage		*3	—	—	V/μs	

*2. High sensitivity (I_{GT}≤10mA) is also available.

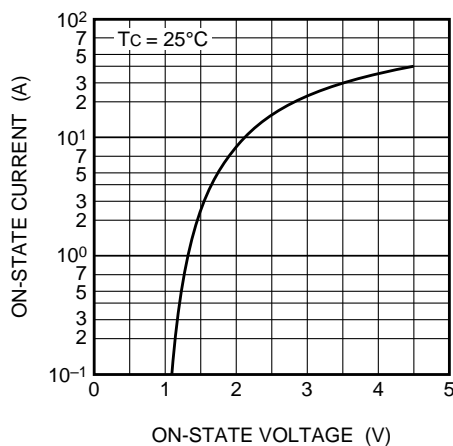
*3. The critical-rate of rise of the off-state commutating voltage is shown in the table below.

*4. Case temperature is measured on the T₂ terminal.

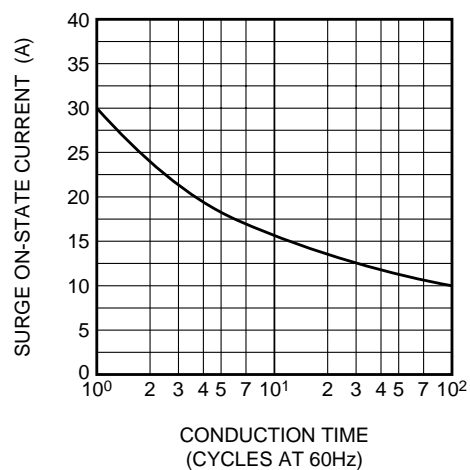
Voltage class	V _{DRM} (V)	(dv/dt) _c		Test conditions	Commutating voltage and current waveforms (inductive load)
		Min.	Unit		
8	400	5	V/μs	1. Junction temperature T _j =125°C 2. Rate of decay of on-state commutating current (di/dt) _c =-1.5A/ms 3. Peak off-state voltage V _D =400V	
12	600				

PERFORMANCE CURVES

MAXIMUM ON-STATE CHARACTERISTICS

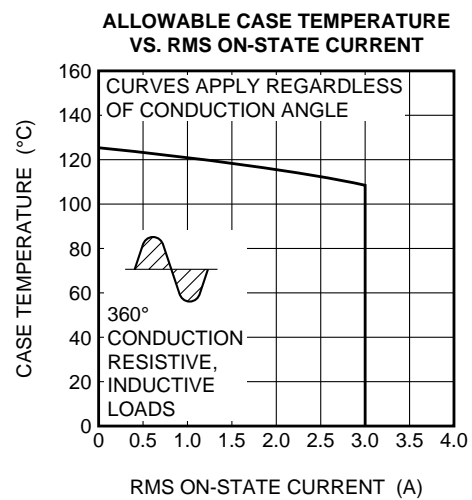
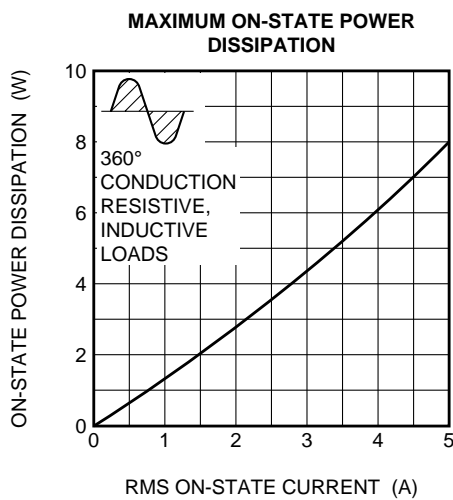
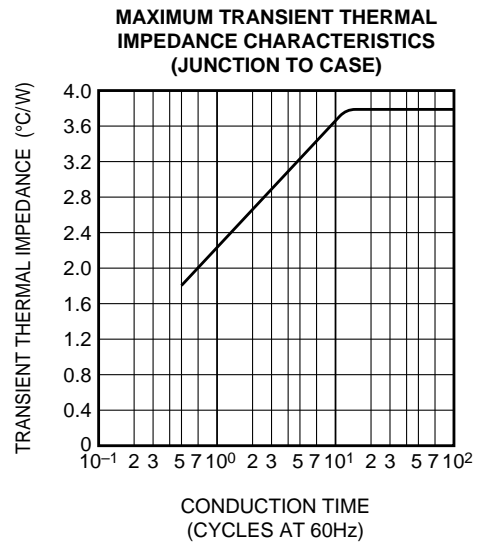
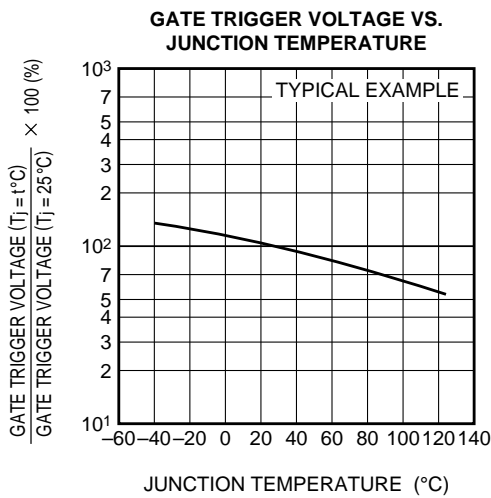
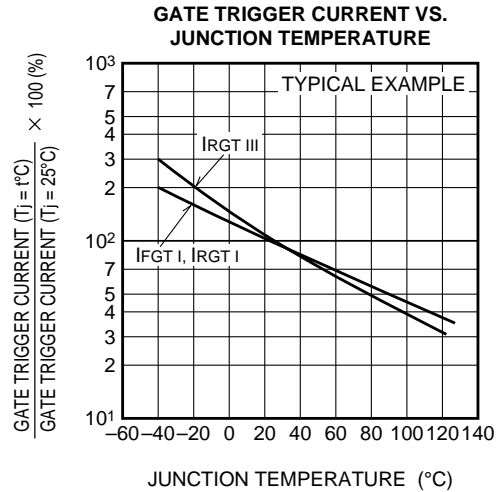
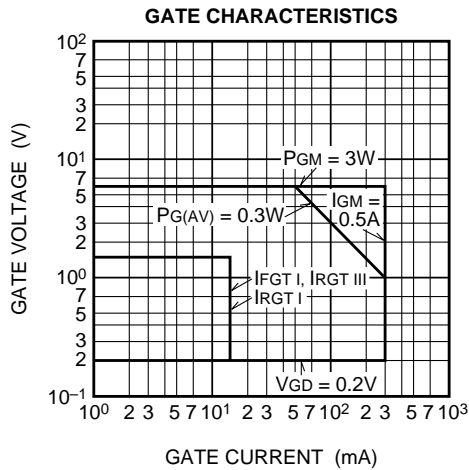


RATED SURGE ON-STATE CURRENT



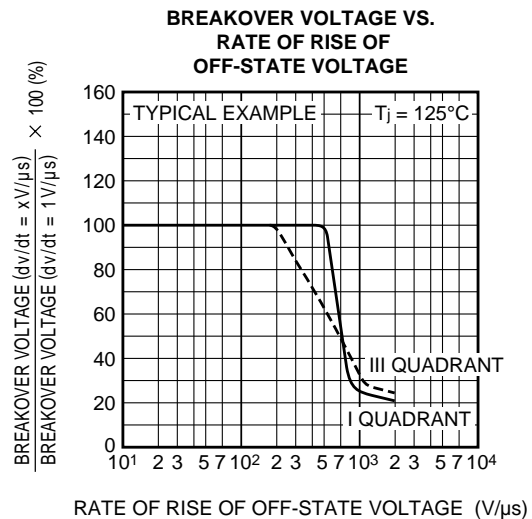
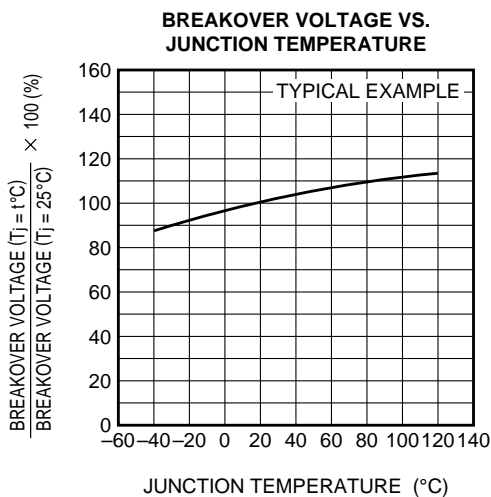
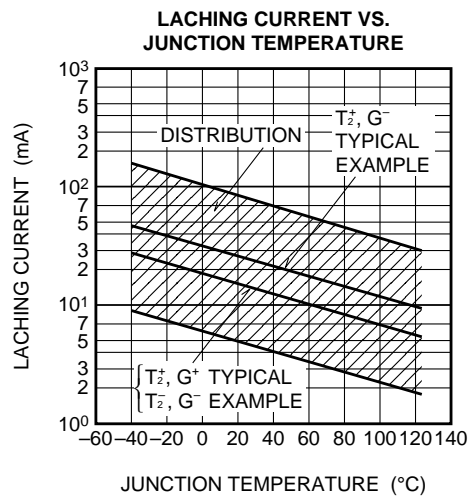
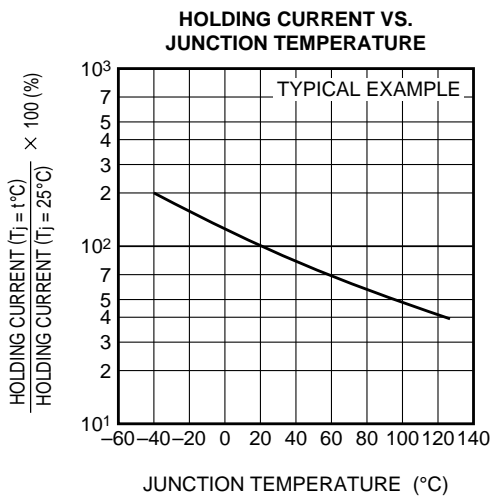
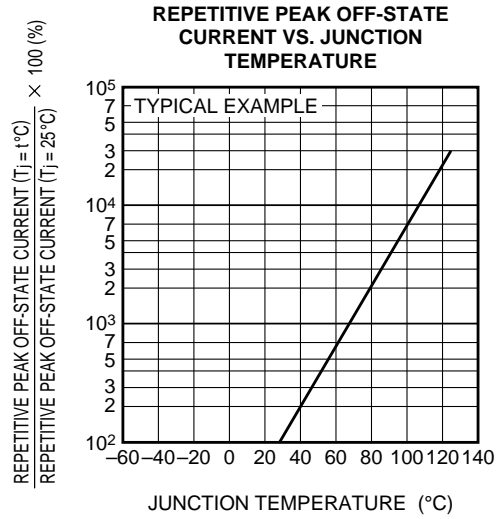
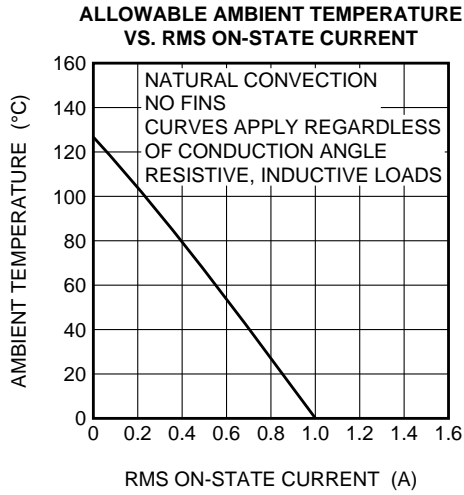
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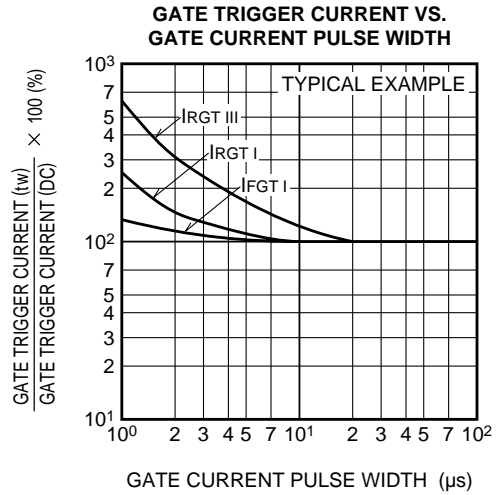
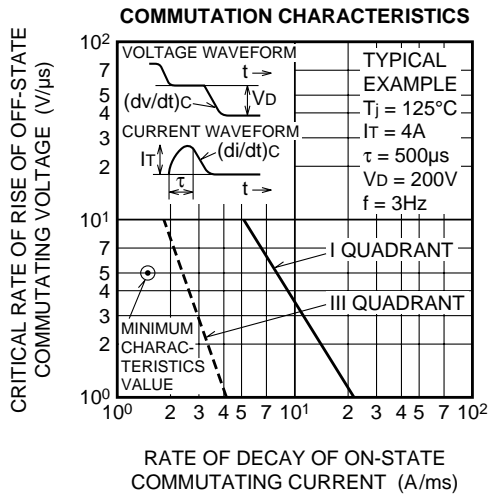
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GATE TRIGGER CHARACTERISTICS TEST CIRCUITS

